PDTC144VE,115 Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	PDTC144VE,115-DG
Manufacturer	NXP USA Inc.
Manufacturer Product Number	PDTC144VE,115
Description	TRANS PREBIAS NPN 50V 0.1A SC75
Detailed Description	Pre-Biased Bipolar Transistor (BJT) NPN - Pre-Biased 50 V 100 mA 150 mW Surface Mount SC-75

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PDTC144VE,115	NXP USA Inc.
Series:	Product Status:
-	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN - Pre-Biased	100 mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50 V	47 kOhms
Resistor - Emitter Base (R2):	DC Current Gain (hFE) (Min) @ Ic, Vce:
10 kOhms	40 @ 5mA, 5V
Vce Saturation (Max) @ Ib, Ic:	Current - Collector Cutoff (Max):
150mV @ 500µA, 10mA	1µA
Power - Max:	Mounting Type:
150 mW	Surface Mount
Package / Case:	Supplier Device Package:
SC-75, SOT-416	SC-75
Base Product Number:	
PDTC144	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

PDTC144V series

NPN resistor-equipped transistors; R1 = 47 kΩ, R2 = 10 kΩ

Rev. 04 — 16 November 2009 Product data sheet

1. Product profile

1.1 General description

NPN resistor-equipped transistors.

Table 1. Product overview

Type number	Package		PNP complement
	NXP	JEITA	
PDTC144VE	SOT416	SC-75	PDTA144VE
PDTC144VK	SOT346	SC-59A	PDTA144VK
PDTC144VM	SOT883	SC-101	PDTA144VM
PDTC144VS[1]	SOT54 (TO-92)	SC-43A	PDTA144VS
PDTC144VT	SOT23	-	PDTA144VT
PDTC144VU	SOT323	SC-70	PDTA144VU

[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- General-purpose switching and amplification
- Inverter and interface circuits
- Circuit drivers

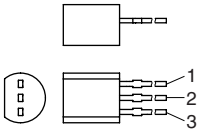
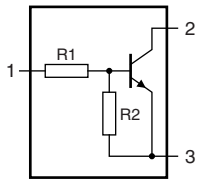
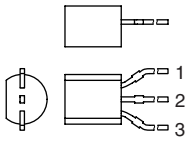
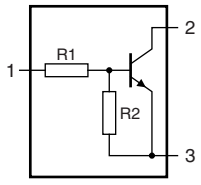
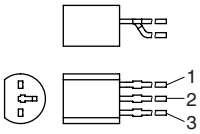
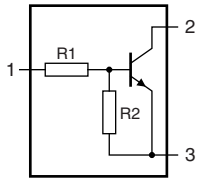
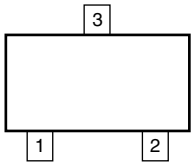
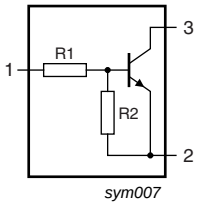
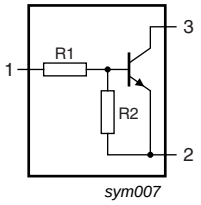
1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I_O	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.17	0.21	0.26	

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)	 001aab347	 006aaa145
2	output (collector)		
3	GND (emitter)		
SOT54A			
1	input (base)	 001aab348	 006aaa145
2	output (collector)		
3	GND (emitter)		
SOT54 variant			
1	input (base)	 001aab447	 006aaa145
2	output (collector)		
3	GND (emitter)		
SOT23, SOT323, SOT346, SOT416			
1	input (base)	 006aaa144	 sym007
2	GND (emitter)		
3	output (collector)		
SOT883			
1	input (base)		 sym007
2	GND (emitter)		
3	output (collector)		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PDTC144VE	SC-75	plastic surface mounted package; 3 leads	SOT416
PDTC144VK	SC-59A	plastic surface mounted package; 3 leads	SOT346
PDTC144VM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 × 0.6 × 0.5 mm	SOT883
PDTC144VS[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PDTC144VT	-	plastic surface mounted package; 3 leads	SOT23
PDTC144VU	SC-70	plastic surface mounted package; 3 leads	SOT323

[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PDTC144VE	18
PDTC144VK	29
PDTC144VM	G6
PDTC144VS	TC144V
PDTC144VT	*AA
PDTC144VU	*18

[1] * = -: made in Hong Kong
* = p: made in Hong Kong
* = t: made in Malaysia
* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	15	V
V_I	input voltage					
	positive			-	+40	V
	negative			-	−15	V
I_O	output current (DC)			-	100	mA
I_{CM}	peak collector current			-	100	mA
P_{tot}	total power dissipation					
	SOT416	$T_{amb} \leq 25$ °C	[1]	-	150	mW
	SOT346	$T_{amb} \leq 25$ °C	[1]	-	250	mW
	SOT883	$T_{amb} \leq 25$ °C	[2][3]	-	250	mW
	SOT54	$T_{amb} \leq 25$ °C	[1]	-	500	mW
	SOT23	$T_{amb} \leq 25$ °C	[1]	-	250	mW
	SOT323	$T_{amb} \leq 25$ °C	[1]	-	200	mW
T_{stg}	storage temperature			−65	+150	°C
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			−65	+150	°C

[1] Refer to standard mounting conditions.

[2] Reflow soldering is the only recommended soldering method.

[3] Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 μm copper strip line.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air					
	SOT416		[1]	-	-	833	K/W
	SOT346		[1]	-	-	500	K/W
	SOT883		[2][3]	-	-	500	K/W
	SOT54		[1]	-	-	250	K/W
	SOT23		[1]	-	-	500	K/W
	SOT323		[1]	-	-	625	K/W

[1] Refer to standard mounting conditions.

[2] Reflow soldering is the only recommended soldering method.

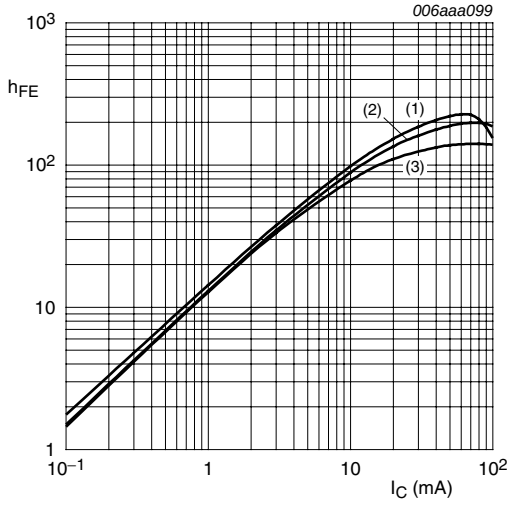
[3] Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 μm copper strip line.

7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = 50 V; I_E = 0 A	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	V_{CE} = 30 V; I_B = 0 A	-	-	1	μA
		V_{CE} = 30 V; I_B = 0 A; T_j = 150 °C	-	-	50	μA
I_{EBO}	emitter-base cut-off current	V_{EB} = 5 V; I_C = 0 A	-	-	150	μA
h_{FE}	DC current gain	V_{CE} = 5 V; I_C = 5 mA	40	-	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA	-	-	150	mV
$V_{I(off)}$	off-state input voltage	V_{CE} = 5 V; I_C = 100 μA	-	3.1	1	V
$V_{I(on)}$	on-state input voltage	V_{CE} = 300 mV; I_C = 2 mA	6	3.8	-	V
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.17	0.21	0.26	
C_c	collector capacitance	V_{CB} = 10 V; I_E = i_e = 0 A; f = 1 MHz	-	-	2	pF



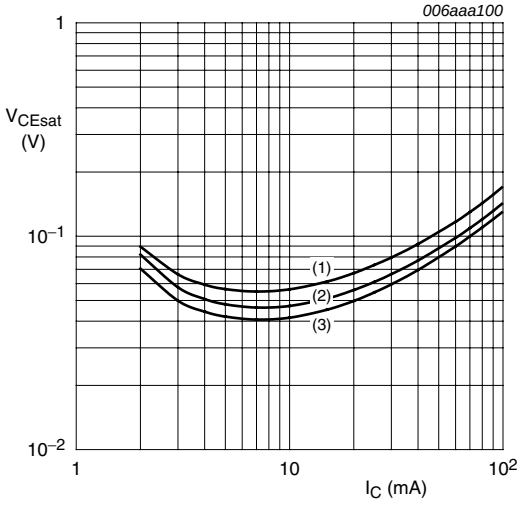
V_{CE} = 5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 1. DC current gain as a function of collector current; typical values



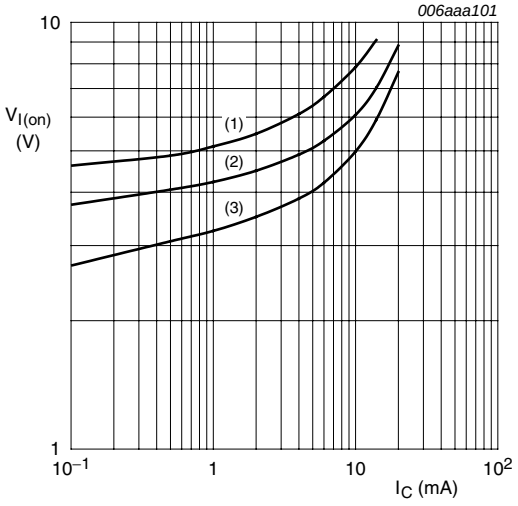
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



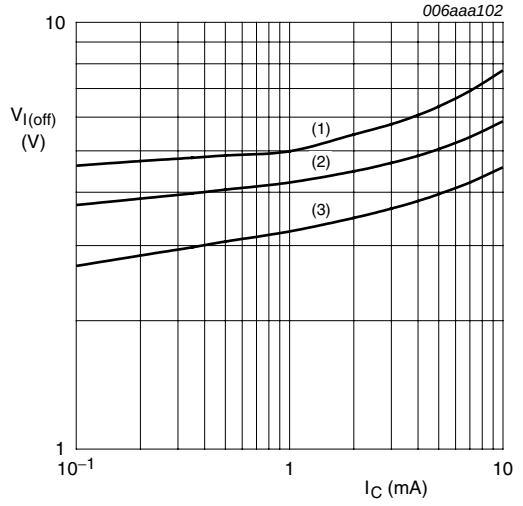
V_{CE} = 0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 3. On-state input voltage as a function of collector current; typical values



V_{CE} = 5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 4. Off-state input voltage as a function of collector current; typical values

8. Package outline

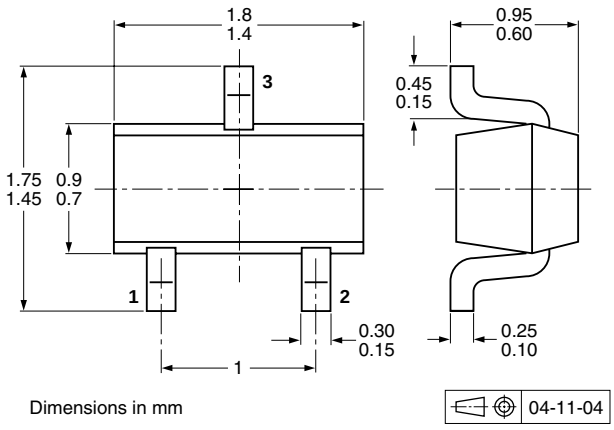


Fig 5. Package outline SOT416 (SC-75)

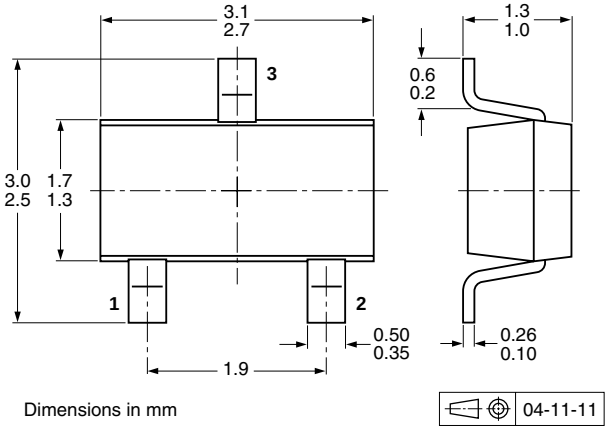


Fig 6. Package outline SOT346 (SC-59A/TO-236)

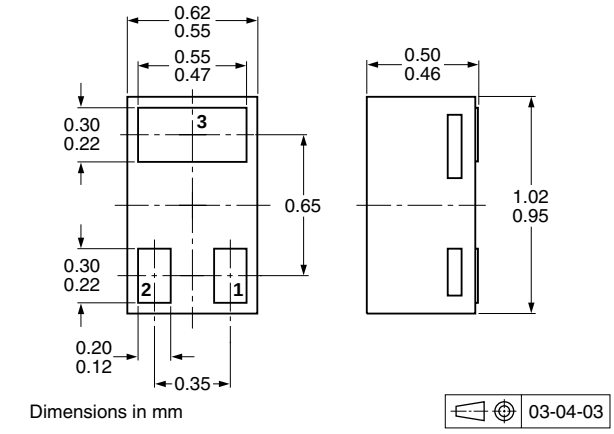


Fig 7. Package outline SOT883 (SC-101)

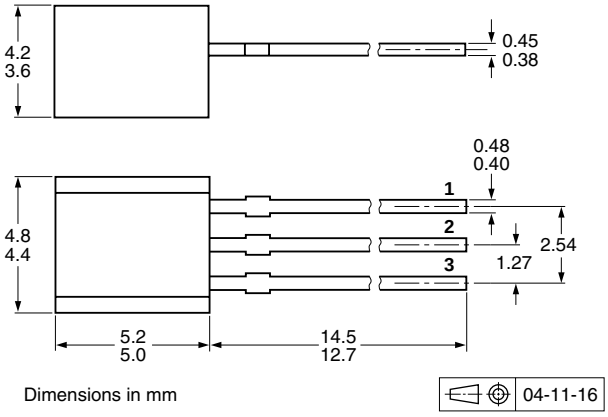


Fig 8. Package outline SOT54 (SC-43A/TO-92)

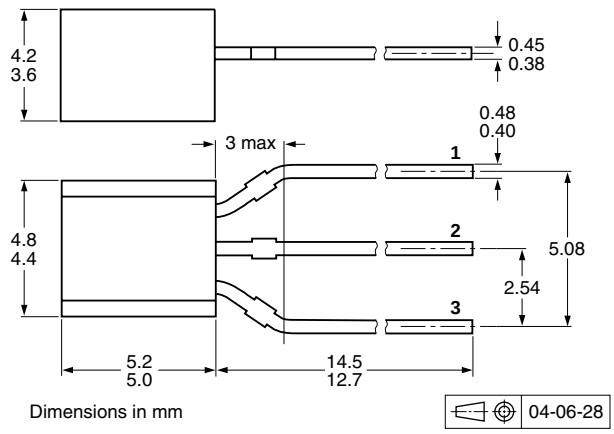


Fig 9. Package outline SOT54A

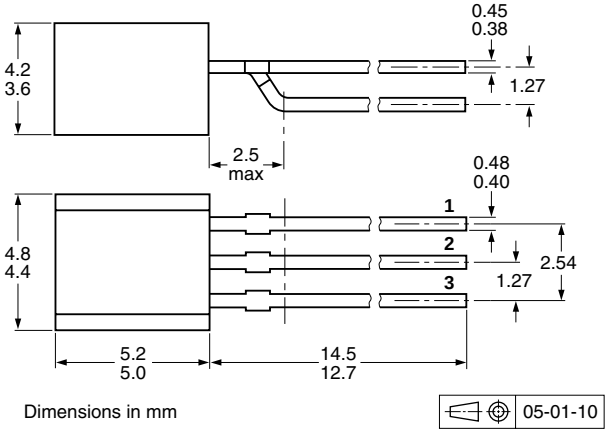


Fig 10. Package outline SOT54 variant

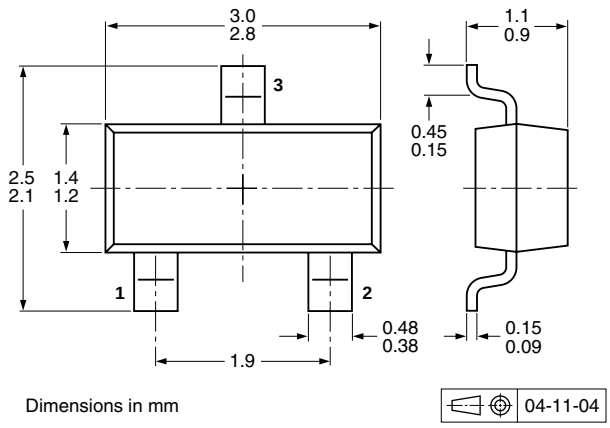


Fig 11. Package outline SOT23 (TO-236AB)

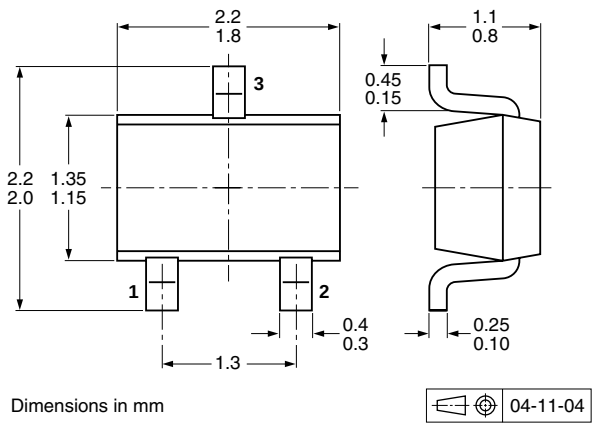


Fig 12. Package outline SOT323 (SC-70)

9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity		
			3000	5000	10000
PDTC144VE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTC144VK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTC144VM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315
PDTC144VS	SOT54	bulk, straight leads	-	-412	-
	SOT54A	tape and reel, wide pitch	-	-	-116
		tape ammopack, wide pitch	-	-	-126
	SOT54 variant	bulk, delta pinning	-	-112	-
PDTC144VT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
PDTC144VU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135

[1] For further information and the availability of packing methods, see Section 12.

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC144V_SER_4	20091116	Product data sheet	-	PDTC144V_SER_3
Modifications:	• This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.			
PDTC144V_SER_3	20050215	Product data sheet	-	PDTC144VT_2
PDTC144VT_2	20040511	Objective data sheet	-	PDTC144VT_1
PDTC144VT_1	20040305	Objective data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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12. Contact information

For more information, please visit: **http://www.nxp.com**

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13. Contents

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Document identifier: PDTC144V_SER_4

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